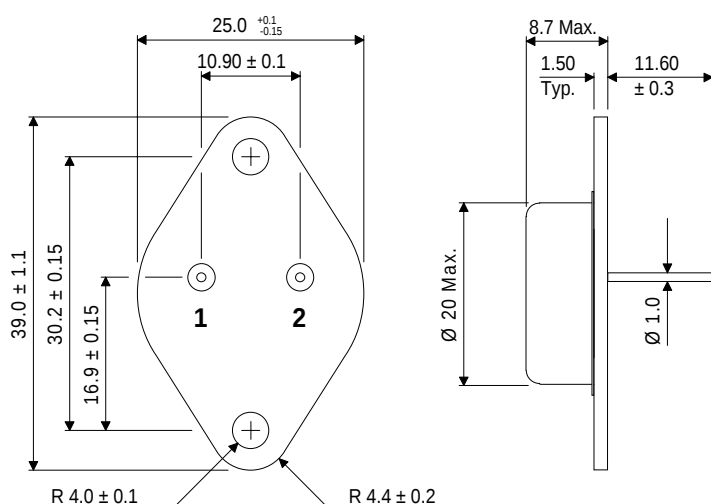


MECHANICAL DATA

Dimensions in mm

N-CHANNEL POWER MOSFET

POWER MOSFETS FOR AUDIO APPLICATIONS



FEATURES

- HIGH SPEED SWITCHING
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (220V & 250V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODES
- COMPLIMENTARY P-CHANNEL BUZ907 & BUZ908

TO-3

Pin 1 – Gate

Pin 2 – Drain

Case – Source

ABSOLUTE MAXIMUM RATINGS

(T_{case} = 25°C unless otherwise stated)

		BUZ902	BUZ903
V _{DSX}	Drain – Source Voltage	220V	250V
V _{GSS}	Gate – Source Voltage	±14V	
I _D	Continuous Drain Current	8A	
I _{D(PK)}	Body Drain Diode	8A	
P _D	Total Power Dissipation @ T _{case} = 25°C	125W	
T _{stg}	Storage Temperature Range	–55 to 150°C	
T _j	Maximum Operating Junction Temperature	150°C	
R _{θJC}	Thermal Resistance Junction – Case	1°C/W	

STATIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSX} Drain – Source Breakdown Voltage	V _{GS} = -10V I _D = 10mA	BUZ902	220			V
		BUZ903	250			V
BV _{GSS} Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100μA	±14			V
V _{GS(OFF)} Gate – Source Cut-Off Voltage	V _{DS} = 10V	I _D = 100mA	0.15		1.5	V
V _{DS(SAT)} * Drain – Source Saturation Voltage	V _{GD} = 0	I _D = 8A			12	V
R _{DS(on)} * Static – Source Resistance	V _{GS} = 10	I _D = 8A			1.5	Ω
I _{DSX} Drain – Source Cut-Off Current	V _{GS} = -10V	V _{DS} = 220V BUZ902			10	mA
		V _{DS} = 250V BUZ903			10	mA
yfs* Forward Transfer Admittance	V _{DS} = 10V	I _D = 3A	0.7		2	S

DYNAMIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C _{iss} Input Capacitance	V _{DS} = 10V f = 1MHz		TBA		pF
C _{oss} Output Capacitance			TBA		
C _{rss} Reverse Transfer Capacitance			TBA		
t _{on} Turn-on Time	V _{DS} = 20V		TBA		ns
t _{off} Turn-off Time	I _D = 5A		TBA		

* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.

